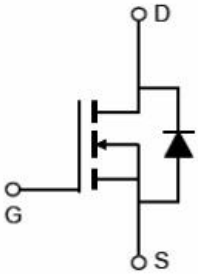
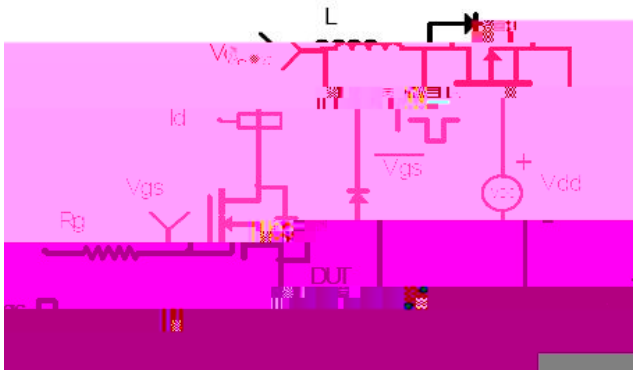
V_{DSS}	85V
R_{DS}(on)	4.2mΩ(typ.)
I_D	120A

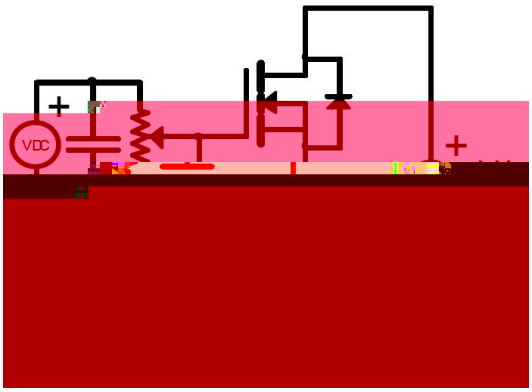


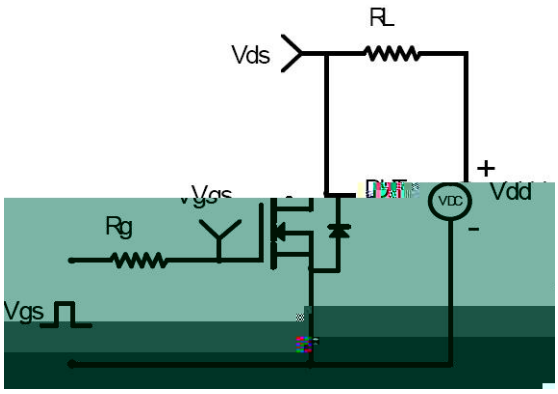
Advanced MOSFET process technology
Special designed for PWM, load switching and general purpose applications
Ultra low on-resistance with low gate charge
Fast switching and reverse body recovery
150 operating temperature

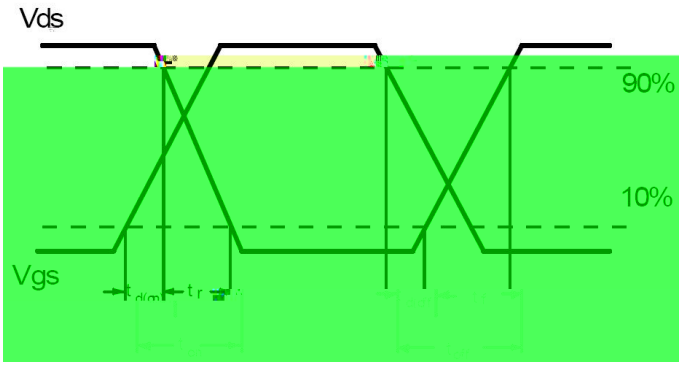
It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	120	A
I_{DM}	Pulsed Drain Current	480	
P_D @T_C = 25°C	Power Dissipation	220	W
V_{DS}	Drain-Source Voltage	85	V
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy @ L=0.1mH	560	mJ
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C







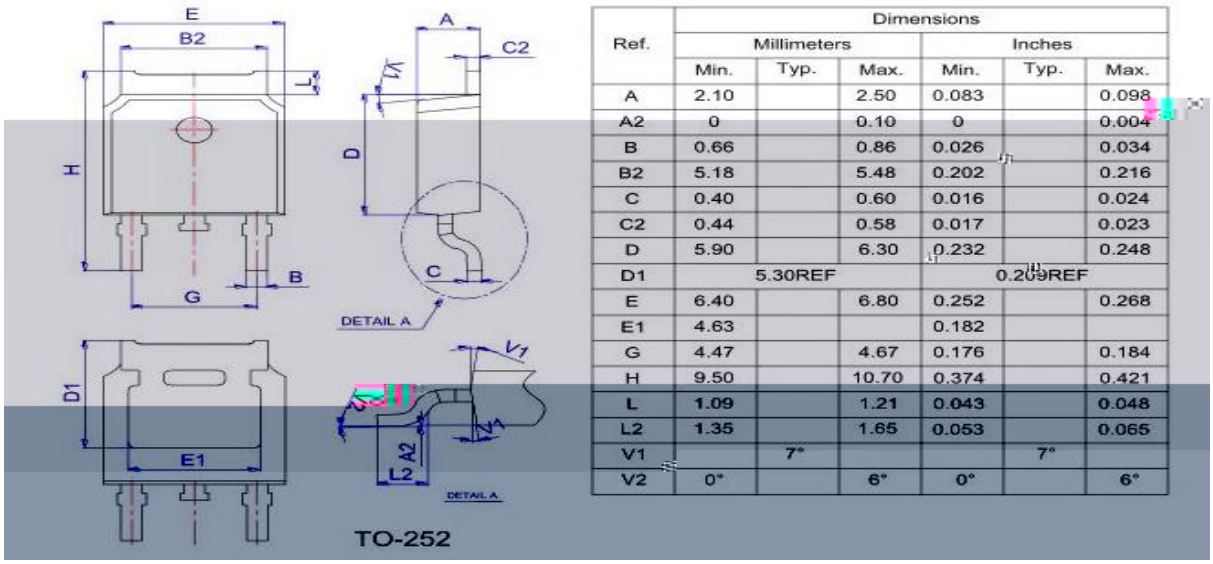


Calculated continuous current based on maximum allowable junction temperature.

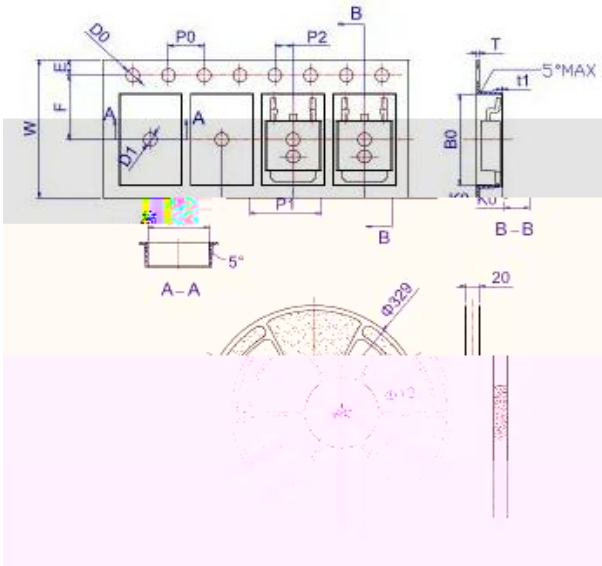
Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation P_D is based on max. junction temperature, using junction-to-case thermal resistance.

The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25 .



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319

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